

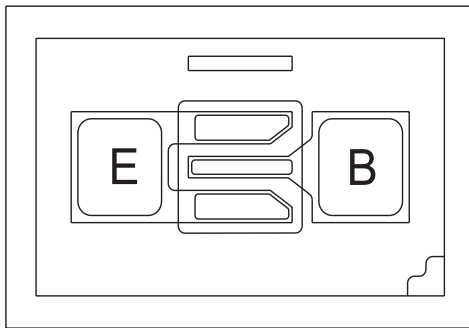
PROCESS CP207
Small Signal Transistor
NPN - Saturated Switch Transistor Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	9.0 x 14 MILS
Die Thickness	8.0 MILS
Base Bonding Pad Area	3.1 x 2.9 MILS
Emitter Bonding Pad Area	3.1 x 2.9 MILS
Top Side Metalization	Al - 13,000Å
Back Side Metalization	Au - 6,000Å

GEOMETRY



BACKSIDE COLLECTOR

R1

GROSS DIE PER 4 INCH WAFER

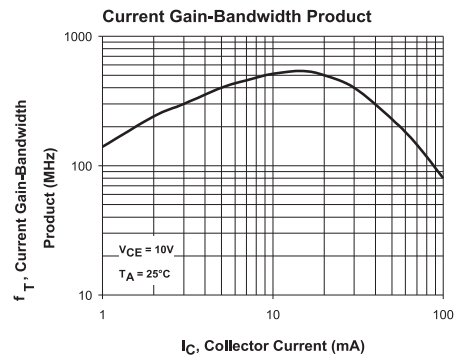
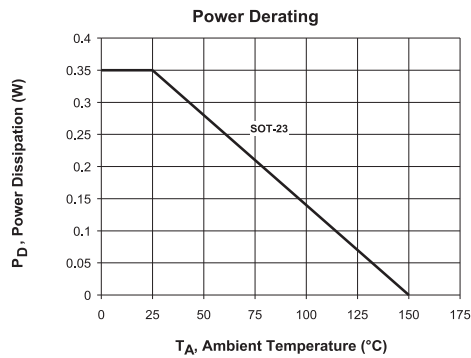
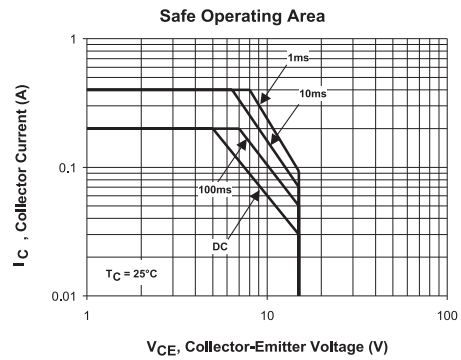
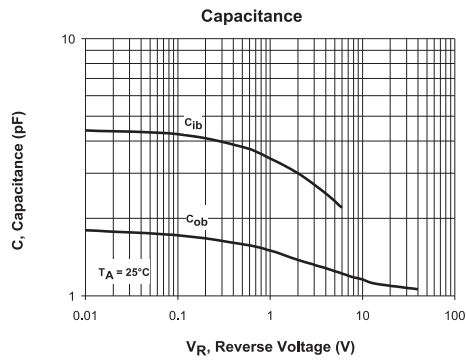
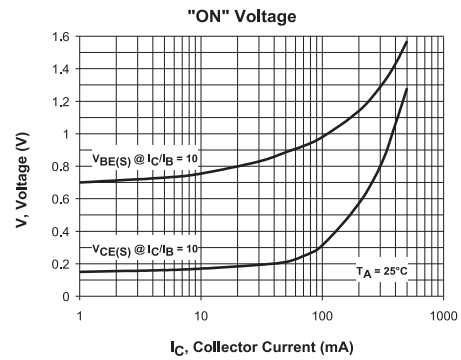
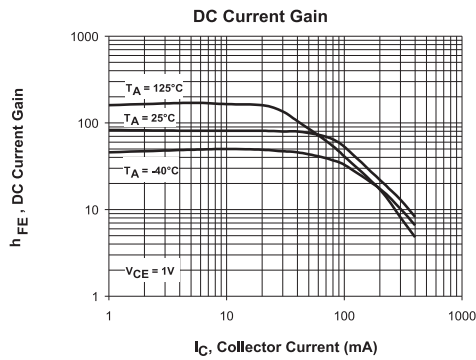
93,430

PRINCIPAL DEVICE TYPES

2N2369A
CMPT2369

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R2 (1-August 2002)



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